

(MASTER)

Year/Number	Title	Primary Author
<u>00-01A</u>	An Evaluation of the Dielectric Isolation Technique for Linear Integrated Circuits	BARRETT, J.C.
<u>00-01B</u>	On Lattice Disorders, Solute Diffusion, Precipitation & Gettering Silicon Devices	
<u>00-02</u>	Electromigration in Integrated Circuits	BLECH, I.A.
<u>00-03</u>	Electronic Conduction in Thermally Grown SiO ₂	LENZLINGER, M.
<u>61-04</u>	Effects of Electrons & Holes on the Transition Layer Characteristics of Linearly Graded p-n Junctions	SAH, C.T.
<u>61-05</u>	Electronic Processes & Excess Currents in Gold-Doped Narrow Silicon Junctions	SAH, C.T.
<u>61-06</u>	A New Semiconductor Tetrode - The Surface-Potential Controlled Transistor	SAH, C.T.
<u>63-07</u>	The Oxidation of Silicon in Dry Oxygen, Wet Oxygen, & Steam	DEAL, B.E.
<u>64-08</u>	Frequency Dependence of the Reverse Biased Capacitance of Gold Doped Silicon p+n Step Junctions	SAH, C.T.
<u>64-09</u>	Theory of Low-Frequency Generation Noise in Junction-Gate Field-Effect Transistors	SAH, C.T.

REPRINT LISTING
(MASTER)

Page 2

(1-ARTICLE MISSING)

Year/Number <i>VOL. + PAGE #</i>	Title	Primary Author
<u>64-10</u> <i>I-11</i>	Dielectric Loss Due to Impurity Cation Migration in a Quartz	SNOW, E.H.
<u>64-11</u> <i>I-12</i>	Simple Physical Model for the Space-Charge Capacitance of Metal-Oxide-Semiconductor Structures	GROVE, A.S.
<u>64-12</u> <i>I-13</i>	Use of Index of Refraction Liquids for the Measurement of the Refractive Index of Thin Transparent Films on Silicon	LEWIS, A.E.
<u>64-13</u> <i>I-14</i>	Plating of Semiconductor & Electronic Devices	DUFFEK, E.F.
<u>64-14</u> <i>I-15</i>	Redistribution of Acceptor & Donor Impurities During Thermal Oxidation of Silicon	GROVE, A.S.
<u>64-15</u> <i>I-16</i>	Luminescence During the Anodic Oxidation of Silicon	WARING, W.
<u>64-16</u> <i>(NOT FOUND)</i>	<u>An Integrated FET Analog Switch</u> <i>(MISSING)</i>	RUEGG, H.W.
<u>64-17</u> <i>I-17</i>	Diffusion of Gallium Through a Silicon Dioxide Layer	GROVE, A.S.
<u>64-18</u> <i>I-18</i>	Simple Analytical Approximations to the Switching Times in Narrow Base Diodes	GROVE, A.S.
<u>65-19</u> <i>I-19</i>	Temperature Dependence of the Superconducting Energy GAP of Thallium Films Determined by Electron Tunneling	BALLONOFF, A.

(MASTER)

Year/Number <i>Vol/PAGE</i>	Title	Primary Author
<u>65-20</u> <i>I-20</i>	Impurity Distribution in Epitaxial Growth	GROVE, A.S.
<u>65-21</u> <i>I-21</i>	Observation of Impurity Redistribution During Thermal Oxidation of Silicon Using the MOS Structure	DEAL, B.E.
<u>65-22</u> <i>I-22</i>	Recent Advances in the Understanding of the Metal-Oxide-Silicon System	DEAL, B.E.
<u>65-23</u> <i>I-23</i>	Source to Drain Resistance Beyond Pinch-Off in Metal-Oxide-Semiconductor Transistors (MOST)	REDDI, V.G.K.
<u>65-24</u> <i>I-24</i>	The Anodic Oxidation of Silicon in Ethylene Glycol Solutions	DUFFEK, E.F.
<u>65-25</u> <i>I-25</i>	A Simplified, Accurate Gold Assay for Plating Baths	LEMONS, K.E.
<u>65-26</u> <i>I-26</i>	Method of Producing Large Si Films for Preselected Imperfection Analysis	LAWRENCE, J.E.
<u>65-27</u> <i>I-27</i>	Observation of Frank-Read Sources in Silicon	
<u>65-28</u> <i>I-28</i>	Thermal Oxidation of Heavily Doped Silicon	DEAL, B.E.
<u>65-29</u> <i>I-29</i>	Electron & Hole Mobilities in Inversion Layers on Thermally Oxidized Silicon Surfaces	LEISTIKO, Jr., O.
<u>65-30</u> <i>I-30</i>	Ion Transport Phenomena in Insulating Films	SNOW, E.H.

REPRINT LISTING

Page 4

(MASTER)

Year/Number <i>Vol./PAGE</i>	Title	Primary Author
<u>65-31</u> <i>I-31</i>	Structure of Drawn & Annealed Tungsten Wire	MEIERAN, E.S.
<u>65-32</u> <i>I-32</i>	Versatile Electron Microscope Reflection Stage & Its Applications	KOEHLER, H.
<u>65-33</u> <i>I-33</i>	Electrical Properties of Copper Segregates in Silicon p-n Junctions	LAWRENCE, J.E.
<u>65-34</u> <i>I-34</i>	Changes in the Phase & Amplitude of Polarized Light Reflected from a Film-Covered Surface & Their Relations with the Film Thickness	KIM, C.K. <i>Sarena A. N.</i>
<u>65-35</u> <i>I-35</i>	Tri-Pyramid & Raised-Triangle (III) Diamond-Lattice Imperfections in Silicon Epitaxial Films	LAWRENCE, J.E.
<u>65-36</u> <i>I-36</i>	Method for Preparing Electron Microscopy Specimens from Selected Details and Its Applications	KOEHLER, H.
<u>65-37</u> <i>I-37</i>	Specimen Storage Magazine for the HU-II High Resolution Diffraction Attachment	KOEHLER, H.
<u>65-38</u> <i>I-38</i>	Tunable High-Pass Filter Characteristics of a Special MOS Transistor	REDDI, V.G.K.
<u>65-39</u> <i>I-39</i>	General Relationship for the Thermal Oxidation of Silicon	DEAL, B.E.
<u>65-40</u> <i>I-40</i>	Stable MOS Transistors	GROVE, A.S.
<u>65-41</u> <i>I-41</i>	The Origin of Channel Currents Associated with p+ Regions in Silicon	GROVE, A.S.

(MASTER)

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>65-42</u> <i>I-42</i>	Electron Microscopy of Polished and Annealed Gallium Arsenide	MEIERAN, E.S.
<u>65-43</u> <i>I-43</i>	Investigation of Thermally Oxidized Silicon Surfaces Using Metal-Oxide-Semiconductor Structures	GROVE, A.S.
<u>65-44</u> <i>I-44</i>	Low-Frequency Generation Noise in Junction Field Effect Transistors	LAURITZEN, P.O.
<u>65-45</u> <i>I-45</i>	The MOS Transistor as an Individual Device and in Integrated Arrays	MOORE, G.C.
<u>66-46</u> <i>I-46</i>	Ionization Threshold in Noise from Silicon Zener Diodes	LAURITZEN, P.O.
<u>66-47</u> <i>I-47</i>	Injection of Minority Carriers at a Field-Induced Junction Near the Si-SiO ₂ Interface	REDDI, V.G.K.
<u>66-48</u> <i>I-48</i>	Polarization Phenomena & Other Properties of Phosphosilicate Glass Films on Silicon	SNOW, E.H.
<u>66-49</u> <i>I-49</i>	Space-Charge Polarization in Glass Films	SNOW, E.H.
<u>66-50</u> <i>I-50</i>	A Model for Radiation Damage in Metal-Oxide Semiconductor Structures	GROVE, A.S.
<u>66-51</u> <i>I-51</i>	Barrier Lowering & Field Penetration at Metal-Dielectric Interfaces. (Al-SiO ₂ ; MOS Structures; E)	MEAD, C.A.
<u>66-52</u> <i>I-52</i>	Mass Transfer in Semiconductor Technology	GROVE, A.S.

(MASTER)

Year/Number	Title	Primary Author
<u>66-53</u> <i>Vol. 1/PAGE 2-53</i>	The Impact of Semiconductors on Ceramics	FORBES, D.W.A.
<u>66-54</u> <i>2-54</i>	Diffusion-Induced Stress & Lattice Disorders in Silicon	LAWRENCE, J.E.
<u>66-55</u> <i>2-55</i>	The Co-Operative Diffusion Effect	LAWRENCE, J.E.
<u>66-56</u> <i>2-56</i>	Mechanisms of Challen Current Formation in Silicon p-n Junctions	FITZGERALD, D.J.
<u>66-57</u> <i>2-57</i>	Properties of the Silicon Dioxide-Silicon System	DEAL, B.E.
<u>66-58</u> <i>2-58</i>	Radiation-Induced Increase in Surface Recombination Velocity of Thermally Oxidized Silicon Structures	FITZGERALD, D.J.
<u>66-59</u> <i>2-59</i>	Temperature Dependence of MOS Transistor Characteristics Below Saturation	VADASZ, L.
<u>66-60</u> <i>2-60</i>	Barrier Energies in Metal-Silicon Dioxide-Silicon Structures	DEAL, B.E.
<u>66-61</u> <i>2-61</i>	Breakdown Voltage of Planar Silicon Junctions	LEISTIKO, Jr., O.
<u>66-62</u> <i>2-62</i>	Contour Deposition - A New Expitaxial Deposition Technique for Semiconductor Devices & Integrated Circuits	KLEIN, T.
<u>66-63</u> <i>2-63</i>	Surface Effects on p-n Junctions. Characteristics of Surface Space-Charge Regions Under Non-Equilibrium Conditions	GROVE, A.S.

REPRINT LISTING
(MASTER)

Page 7

1- ARTICLE MISSING

Year/Number <i>vol./page</i>	Title	Primary Author
<u>67-64</u> <i>5-64</i>	Measurement of the Drift Velocity of Holes in Silicon at High-Field Strengths	RODRIGUEZ, V.
<u>67-65</u> <i>5-65</i>	Anistropy Constant of 50:50 Ni-Co Alloy Films	CARTER, W.S.
<u>67-66</u> <i>5-66</i>	Characteristics of the Surface-State Charge (Q_{SS}) of Thermally Oxidized Silicon	DEAL, B.E.
<u>67-67</u> <i>5-67</i>	Effect of Surface Fields on the Breakdown Voltage of Planar Silicon p-n Junctions	GROVE, A.S.
<u>67-68</u> <i>5-68</i>	An Optimized Avalanche Photodiode	RUEGG, H.W.
<u>67-69</u> <i>(NOT FOUND)</i>	<u>An Epitaxial GaAs Field-Effect Transistor</u> <i>(MISSING)</i>	HOOPER, W.W.
<u>67-70</u> <i>5-70</i>	Effects of Ionizing Radiation on Oxidized Silicon Surfaces & Planar Devices	SNOW, E.H.
<u>67-71</u> <i>5-71</i>	Properties of Gold Doped MOS Structures	CAGNINA, S.F.
<u>67-72</u> <i>5-72</i>	Fowler-Nordheim Tunneling in SiO_2 Films	SNOW, E.H.
<u>67-73A</u> <i>5-73A</i>	Stacking Fault Contrast in X-Ray Topographs of Annealed Si Web Dendrite	MEIERAN, E.S.
<u>67-73B</u> <i>5-73B</i>	Influence of Surface Conditions on Silicon Planar Transistor Current Gain	REDDI, V.G.K.

(MASTER)

Year/Number	Title	Primary Author
<u>68-74</u>	On the Effect of Mobility Variation on MOS Device Characteristics	FROMAN-BENTCH-KOWSKY, D.
<u>68-75</u>	Surface Recombination in Semiconductors	FITZGERALD, D.J.
<u>68-76</u>	Comparison of Surface & Bulk Effects of Nuclear Reactor Radiation on Planar Devices	FITZGERALD, D.J.
<u>68-77</u>	Electrical Properties of Vapor-Deposited Silicon Nitride & Silicon Oxide Films	DEAL, B.E.
<u>68-78</u>	Evaluation of Bulk & Epitaxial GaAs by Means of X-Ray Topography	MEIERAN, E.S.
<u>68-79</u>	Majority Carrier Surface Mobilities in Thermally Oxidized Silicon	REDDI, V.G.K.
<u>68-80</u>	Metallographic Analysis of Gettered Silicon	LWARENCE, J.E.
<u>68-81</u>	Photoemission Studies of the Electronic Structure of Cobalt	SPICER, W.E.
<u>68-82</u>	Polarization Effects in Insulating Films on Silicon--A Review	SNOW, E.H.
<u>68-83</u>	Transverse Negative Differential Mobilities for Hot Electrons & Domain Formation in Germanium	SHYAM, M.
<u>68-84</u>	Surface-State Related 1/f Noise in p-n Junctions & MOS Transistors	HSU, S.T.

REPRINT LISTING

Page 9

(MASTER)

Year/Number	Title	Primary Author
<u>68-85</u> <i>Vol. 1 Mar I-85</i>	Surface Effects on Metal-Silicon Contacts	YU, A.Y.C.
<u>68-86</u> <i>I-86</i>	Behavior of Dislocations in Silicon Semiconductor Devices. Diffusion, Electrical.	LAWRENCE, J.E.
<u>68-87</u> <i>I-87</i>	DC Analysis of an MOS Source Follower	FROMAN-BENTCHKOWSKY, D.
<u>68-88</u> <i>I-88</i>	A Method for Determining Sodium Content of Semiconductor Processing Materials	YURASH, B.
<u>68-89</u> <i>I-89</i>	The Effect of Illumination of Gunn Oscillations in Epitaxial GaAs	HAYDL, W.H.
<u>68-90A</u> <i>I-90A</i>	The Gunn Effect Under Imperfect Cathode Boundary Conditions	KROEMER, H.
<u>68-90B</u> <i>I-90B</i>	Photoemission & Optical Studies of the Electronic Structure of Palladium	SPICER, W.E.
<u>68-91A</u> <i>I-91A</i>	Contrast Asymmetries in Lang Topographs of Crystals Strained by Thin Films	MEIERAN, E.S.
<u>68-91B</u> <i>I-91B</i>	Advances in Doped Oxides as Diffusion Sources	BARRY, M.L.
<u>69-92A</u> <i>I-92A</i>	Conductance of MOS Transistors in Saturation	FROMAN-BENTCHKOWSKY, D.
<u>69-92B</u> <i>I-92B</i>	Ohmic Contacts to Semiconductors	

REPRINT LISTING

Page 10

(MASTER)

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>69-93</u> <i>I-93</i>	Current Gain & Cutoff Frequency Fallout at High Currents	WHITTIER, R.J.
<u>69-94</u> <i>I-94</i>	Fowler-Nordheim Tunneling into Thermally Grown SiO ₂	LENZLINGER, M.
<u>69-95</u> <i>I-95</i>	Electromigration in Thin Al Films	BLECH, I.A.
<u>69-96</u> <i>I-96</i>	Computer Aided Design & Character- ization of Digital MOS Integrated Circuits	FROMAN- BENTCHKOWSKY, D.
<u>69-97</u> <i>I-97</i>	Forward Current-Voltage & Switching Characteristics of p-n-n (Epitaxial) Diodes	DUTTON, R.W.
<u>69-98A</u> <i>I-98A</i>	Investigation of Waveguide-Below- Cutoff Resonators for Solid-State Active Devices	IVANEK, F.
<u>69-98B</u> <i>I-98B</i>	Direct Video Imaging of X-Ray Topographs	LANDRE, J.K.
<u>69-99</u> <i>I-99</i>	An Integrated Metal-Nitride-Oxide- Silicon (MNOS) Memory	FROMAN- BENTCHKOWSKY, D.
<u>69-100</u> <i>I-100</i>	Doped Oxides as Diffusion Sources. I. Boron into Silicon	BARRY, M.L.
<u>69-101</u> <i>I-101</i>	Technology & Performance of Inte- grated Complementary MOS Circuits	KLEIN, T.
<u>69-102</u> <i>I-102</i>	Characteristics of Fast Surface States Associated with SiO ₂ -Si & Si ₃ N ₄ -SiO ₂ Si Structures	DEAL, B.E.

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>69-103</u> <i>I-103</i>	Charge Transport and Storage in Metal-Nitride-Oxide-Silicon (MNOS) Structures	FROMAN-BENTCHKOWSKY, D.
<u>69-104</u> <i>I-104</i>	Phosphorus and Arsenic Doping of Epitaxial Silicon Films in the 1000° to 1200°C Temperature Range	SWANSON, T.B.
<u>69-105</u> <i>NOT FOUND</i>	<i>(MISSING)</i> Hall Effect in Silicon-Chromium Films	LENZLINGER, M.
<u>69-106</u> <i>I-106</i>	Radiation Effects on Silicon Schottky Barriers	YU, A.Y.C.
<u>69-107</u> <i>I-107</i>	Characterization of Burst Noise in Silicon Devices	HSU, S.T.
<u>69-108</u> <i>I-108</i>	Minority Carrier Injection of Metal-Silicon Contacts	YU, A.Y.C.
<u>69-109</u> <i>I-109</i>	Surface-Charge Induced Failures Observed on MOS Integrated Circuits	FORSYTHE, D.D.
<u>70-110</u> <i>I-110</i>	Some Recent Developments in Fused Glass Films on Semiconductor Devices	DUMESNIL, M.
<u>70-111</u> <i>I-111</i>	Further Verification of a Model for Diffusion from Doped Oxides	BARRY, M.L.
<u>70-112</u> <i>I-112</i>	Technology for the Design of Low Power Circuits	BITTMAN, C.A.
<u>70-113</u> <i>I-113</i>	Structural Properties of Vapor Deposited Silicon Nitride	KOELLER, H. KOHLER , W.A.

REPRINT LISTING

Page 12

(MASTER)

2 - MISSING

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>70-114</u> <i>I-114</i>	The Metal-Semiconductor Contact: An Old Device With a New Future	YU, A.Y.C.
<u>70-115</u> <i>I-115</i>	Avalanche Injection & Second Break- down in Transistors	HOWER, P.L.
<u>70-116</u> <i>NOT FOUND</i>	<i>(MISSING)</i> C.W. Operation of L.S.A. Oscillators in R Band	SHYAM, M.
<u>70-117</u> <i>I-117</i>	A Continuous Process for the Deposition of Silicon Oxide from the Oxidation of Silane	BARRY, M.L.
<u>70-118</u> <i>I-118</i>	Diffusion from Doped-Oxide Sources	BARRY, M.L.
<u>70-119</u> <i>I-119</i>	Measurement & Control of Dielectric Film Properties During Semiconductor Device Processing	DEAL, B.E.
<u>70-120</u> <i>I-120</i>	A Study of Diffused Layers of Arsenic and Antimony in Silicon Using the Ion-Scattering Technique	CHOU, C.
<u>70-121</u> <i>I-121</i>	Low-Frequency Excess in Metal-Silicon Schottky Barrier Diodes	HSU, S.T.
<u>70-122</u> <i>NOT FOUND</i>	<i>(MISSING)</i> Self-Scanned Photosensor Arrays	DYCK, R.H.
<u>70-123</u> <i>I-123</i>	Silicon Defect Structure Induced by Arsenic Diffusion and Subsequent Steam Oxidation	DASH, S.
<u>70-124</u> <i>I-124</i>	The Metal-Nitride-Oxide-Silicon (MNOS) Transistor-Characteristics and Applications	FROMAN- BENTCHKOWSKY, D.

REPRINT LISTING
(MASTER)

Year/Number <i>vol./page</i>	Title	Primary Author
<u>70-125</u> <i>I-125</i>	Avalanche Degradation of h_{FE}	McDONALD, B.A.
<u>70-126</u> <i>I-126</i>	Doped Oxides as Diffusion Sources. II. Phosphorus into Silicon	BARRY, M.L.
<u>70-127</u> <i>I-127</i>	Design & Performance of the GaAs FET	BECHTEL, N.G.
<u>70-128</u> <i>I-28</i>	Thermal Oxidation of Polycrystalline Silicon Films	KAMINS, T.I.
<u>70-129</u> <i>I-129</i>	Carrier Accumulation & Space-Charge-Limited Current Flow in Field-Effect Transistors	
<u>70-130</u> <i>NOT FOUND</i>	<i>(MISSING)</i> Characteristics of Aluminum-Silicon Schottky Barrier Diode	YU, A.Y.C.
<u>70-131</u> <i>NOT FOUND</i>	<i>(MISSING)</i> Electron Tunneling & Contact Resistance of Metal-Silicon Contact Barriers	YU, A.Y.C.
<u>70-132</u> <i>I-132</i>	Physical Model for Burst Noise in Semiconductor Devices	HSU, S.T.
<u>70-133</u> <i>I-133</i>	Silicon Gate Technology	FAGGIN, F.
<u>70-134</u> <i>I-134</i>	Sodium Migration Through Electron-Gun Evaporated Al_2O_3 & Double Layer Al_2O_3 - SiO_2 Structures	ABBOTT, R.A.
<u>70-135</u> <i>I-135</i>	Surface State Related 1/f Noise in MOS Transistors	HSU, S.T.
<u>70-136</u> <i>NOT FOUND</i>	<i>(MISSING)</i> Surface State Related 1/f Noise in p-n Junctions	HSU, S.T.

REPRINT LISTING

Page 14

(MASTER)

2 MISSING

Year/Number Vol./PAGE	Title	Primary Author
<u>70-137</u> NOT FOUND	(MISSING) The Effects of Lateral Injection & Base-Widening on the High Current-Low Voltage Characteristics of Transistors	WHITTIER, R.J.
<u>71-138</u> I-138	The Effects of Epoxy Encapsulant Composition on Semiconductor Device Stability	OLBERG, R.C.
<u>71-139</u> I-139	Low-Temperature Reduction of Fast Surface States Associated with Thermally Oxidized Silicon	CASTRO, P.L.
<u>71-140</u> I-140	Gate Protection of MIS Devices	LENZLINGER, M.
<u>71-141</u> I-141	Reduction of Electromigration-Induced Failure in Aluminum Metallization Through Anodization	LEARN, A.J.
<u>71-142</u> I-142	Video Display of X-Ray Images: I. X-Ray Topographs	MEIERAN, E.S.
<u>71-143</u> I-143	Video Display of X-Ray Images: II. Laue Patterns	MEIERAN, E.S.
<u>71-144</u> NOT FOUND	(MISSING) Electromigration in Al/Cu/Al Films Observed by Transmission Electron Microscopy	HOROWITZ, S.J.
<u>71-145</u> I-145	Anodization of Aluminum to Inhibit Hillcock Growth During High Temperature Processing	DELL'OCA, C.J.
<u>71-146</u> I-146	Alloying Behavior of Au & Au-Ge on GaAs.	GYULAI, J.

(MASTER)

Year/Number	Title	Primary Author
<u>71-147</u>	Charge Transfer in Charge-Coupled Devices	FROMAN-BENTCHKOWSKY, D.
<u>71-148</u>	Degradation of h_{FE} at Moderate Current Levels	MCDONALD, B.A.
<u>71-149</u>	Current Concepts in the Passivation & Encapsulation of Semiconductor Devices	DEAL, B.E.
<u>71-150</u>	The Applications of Scanning & Transmission Electron Microscopy in the Semiconductor Industry	MEIERAN, E.S.
<u>71-151</u>	Effect of Redundant Microstructure on Electromigration-Induced Failure	LEARN, A.J.
<u>71-152</u>	Hall Mobility in Chemically Deposited Polycrystalline in Silicon	KAMINS, T.I.
<u>71-153</u>	Silicide Resistors for Integrated Circuits	WAITS, R.K.
<u>71-154</u>	h_{FE} Fallout at Low Temperatures	GOPIN, H.J.
<u>71-155</u>	An Investigation of Lateral Transistors - D.C. Characteristics	CHOU, C.
<u>71-156</u>	Ionic Contamination - Induced Degradation of low Current h_{FE}	MCDONALD, B.A.
<u>71-157</u>	Simple Determination of the Base Transport Factor of Bipolar Transistors	DOWNING, J.P.

REPRINT LISTING

Page 16

(MASTER)

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>71-158</u> <i>I-158</i>	Channeling of Phosphorus Ions in Silicon	REDDI, V.G.K.
<u>72-159</u> <i>III-159</i>	Diffusion of Impurities in Polycrystalline Silicon	KAMINS, T.I.
<u>72-160A</u> <i>III-160A</i>	In-Process Thickness Monitor for Polycrystalline Silicon Deposition	KAMINS, T.I.
<u>72-160B</u> <i>III-160B</i>	Ion Implantation for Silicon Device Fabrication	REDDI, V.G.K.
<u>72-161</u> <i>III-161</i>	Non-Destructive Thickness Determination of Polycrystalline Silicon Deposited on Oxidized Silicon	DELL'OCA, C.J.
<u>72-162</u> <i>III-162</i>	Errata: Erratum: Electromigration in Thin Al Films	BLECH, I.A.
<u>72-163</u> <i>III-163</i>	High-Intensity Transmission X-Ray Topography of Homogeneously Bent Crystals	MEIERAN, E.S.
<u>72-164</u> <i>III-164</i>	A New Dielectric Isolation Technique for Bipolar Integrated Circuits Using Thin Single-Crystal Silicon Films	KAMINS, T.I.
<u>72-165</u> <i>III-165</i>	The Suppression of Ionic Contamination During Silicon Nitride Deposition	MacKENNA, E.L.
<u>72-166</u> <i>III-166</i>	Field-Effects in Polycrystalline-Silicon Films	KAMINS, T.I.

(MASTER)

Year/Number <i>VOL./PAGE</i>	Title	Primary Author
<u>72-167</u> <i>III-167</i>	p-n Junctions in Polycrystalline-Silicon Films	MANOLIU, J.
<u>72-168</u> <i>III-168</i>	Resistivity of Chemically Deposited Polycrystalline-Silicon	JOSEPH, J.D.
<u>72-169</u> <i>III-169</i>	Small-Signal Characteristics of Lateral Transistors	CHOU, C.
<u>72-170</u> <i>III-170</i>	The Combination of Silicon Nitride and Aluminum Anodization for Semiconductor Device Passivation	DELL'OCA, C.J.
<u>73-171</u> <i>III-171</i>	Effect of Structure & Processing on Electromigration-Induced Failure in Anodized Aluminum	LEARN, A.J.
<u>73-172</u> <i>III-172</i>	High-Resolution SEM Observation of Semiconductor Device Cross-Sections	MEIERAN, E.S.
<u>73-173</u> <i>III-173</i>	Limitations of High-Temperature Processing of Aluminum-Copper Metallization	LEARN, A.J.
<u>73-174</u> <i>III-174</i>	Structure of Chemically Deposited Polycrystalline-Silicon Films	KAMINS, T.I.
<u>73-175</u> <i>III-175</i>	Anomalous Residual Damage in Si After Annealing of "Through-Oxide" Arsenic Implantations	CASS, T.R.
<u>73-176</u> <i>III-176</i>	Channeling and DeChanneling of Ion-Implanted Phosphorus in Silicon	REDDI, V.G.K.
<u>73-177</u> <i>III-177</i>	Subnanosecond Emitter-Coupled Logic Gate Circuit Using Isoplanar II.	DHAKA, V.A.

(MASTER)

Year/Number	Title	Primary Author
<u>73-178</u>	X-Ray Measurements of stress in Thin Single-Crystal Silicon Films.	KAMINS, T.I.
<u>74-179</u>	Diffusion in Thin Silicon Films Formed by Electrochemical Etching	KAMINS, T.I.
<u>74-180</u>	Electromigration Effects in Aluminum Alloy Metallization.	LEARN, A.J.
<u>74-181</u>	Aluminum Alloy Film Deposition and Characterization	LEARN, A.J.
<u>74-182</u>	Gettering and Dislocations	DASH, S.
<u>74-183</u>	Deformation Occurring During the Deposition of Polycrystalline-Silicon Films	KAMINS, T.I.
<u>74-184</u>	The Current Understanding of Charges in the Thermally Oxidized Silicon Structure	DEAL, B.E.
<u>74-185</u>	Hall Mobility in Dielectrically Isolated Single-Crystal Silicon Films Defined by Electrochemical Etching	KAMINS, T.I.
<u>74-186</u>	Minority-Carrier Lifetime in Dielectrically Isolated Single-Crystal Silicon Films Defined by Electrochemical Etching	KAMINS, T.I.
<u>74-187</u>	Chemically Vapor Deposited Polycrystalline-Silicon Films	KAMINS, T.I.

(MASTER)

Year/Number <i>VOL./PAGE</i>	Title	Primary Author
<u>75-188</u> <i>III-188</i>	Kinetics of the Thermal Oxidation of Silicon in O ₂ /N ₂ Mixtures at 1200°C	HESS, D.W.
<u>75-189</u> <i>III-189</i>	Characteristics of Si-SiO ₂ Interfaces Beneath Thin Silicon Films Defined by Electrochemical Etching	KAMINS, T.I.
<u>75-190</u> <i>III-190</i>	Effects of MOS Metallization Geometry and Processing on Mobile Impurities	LEARN, A.J.
<u>75-191</u> <i>III-191</i>	Effect of Nitrogen and Oxygen/Nitrogen Mixtures on Oxide Charges in MOS Structures	HESS, D.W.
<u>76-192</u> <i>NOT FOUND</i>	<i>(MISSING)</i> Studies of the Ti-W Metallization System on Si	NOWICKI, R.S. (co-author)
<u>76-193</u> <i>III-193</i>	Identification of Integrated Circuit Process Areas Amenable to Diagnosis and Control by Analytical Beam Techniques	DEAL, B.E.
<u>76-194</u> <i>III-194</i>	Evolution and Current Status of Aluminum Metallization	LEARN, A.J.
<u>76-195</u> <i>III-195</i>	MOS Electrode Size Effects	LEARN, A.J.
<u>76-196</u> <i>III-196</i>	Initial Stages of Oxide Growth and Pore Initiation in the Porous Anodization of Aluminum	DELL'OCA, C.J.
<u>77-197</u> <i>III-197</i>	Effects of Ion Implantation on Charges in the Silicon-Silicon Dioxide System	LEARN, A.J.

(MASTER)

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>77-198</u> <i>II-198</i>	Effects of Oxidation and Nitrogen Annealing on Ion Implantation Induced Interface States in the Silicon-Silicon Dioxide System	HESS, D.W.
<u>77-199</u> <i>III-199</i>	Kinetics of the Thermal Oxidation of Silicon in O ₂ /HCl Mixtures (JES 124, 736 (1977)).	HESS, D.W.
<u>77-200</u> <i>III-200</i>	Effect of Chlorine on the Negative Bias Instability in MOS Structures (JES 124, 740 (1977)).	HESS, D.W.
<u>77-201</u> <i>III-201</i>	New Developments in Materials and Processing Aspects of Silicon Device Technology (Japan, JAP 16, 29 (1977)).	DEAL, B.E.
<u>77-202</u> <i>III-202</i>	Investigation of Silicon Etching and Silicon Dioxide Bubble Information Formation During Silicon Oxidation in HCl-Oxygen Atmospheres (Thin Solid Films, 42, 127 (1977)).	HESS, D.W.
<u>77-203</u> <i>III-203</i>	Reflections on the Past and Thoughts About the Future of Semiconductor Technology	HOGAN, C.L.
<u>77-204</u> <i>III-204</i>	Charge Effects and Other Properties of the Si-SiO ₂ Interface: The Current Understanding (Proc. 3rd. Int'l. Symp. on Si Mtls Sci & Technology)	DEAL, B.E.
<u>77-205</u> <i>III-205</i>	Kinetics of the Thermal Oxidation of Silicon in O ₂ /H ₂ O and O ₂ /Cl ₂ Mixtures	DEAL, B.E.

(MASTER)

Year/Number <i>Vol. / Page</i>	Title	Primary Author
<u>78-206</u> <i>II-206</i>	Thermal Oxidation of Heavily Phosphorus-Doped Silicon	DEAL, B.E. (co-author)
<u>78-207</u> <i>II-207</i>	Thermal Oxidation Kinetics of Silicon in Pyrogenic H ₂ O and 5% HCl/H ₂ O Mixtures	DEAL, B.E.
<u>78-208</u> <i>III-208</i>	Silicon Epitaxy and Oxidation	DEAL, B.E. (co-author)
<u>78-209</u> <i>III-209</i>	Chlorine Concentration Profiles in O ₂ /HCl and H ₂ O/HCl Thermal Silicon Oxides Using SIMS	DEAL, B.E.
<u>79-210</u> <i>II-210</i>	The Evolution of Silicon Semiconductor Technology: 1952-1977	DEAL, B.E.
<u>79-211</u> <i>III-211</i>	Properties and Measurements of Charges Associated with the Thermally Oxidized Silicon System	DEAL, B.E.
<u>79-212</u> <i>II-212</i>	Dependence of Interface State Density on Silicon Thermal Oxidation Process Variables	RAZOUK, R.R.
<u>79-213</u> <i>II-213</i>	Low Temperature Differential Oxidation for Double Polysilicon VLSI Devices	BARNES, J.J.
<u>79-214</u> <i>III-214</i>	ESR Centers, Interface States, and Oxide Fixed Charge in Thermally Oxidized Silicon Wafers	DEAL, B.E. (co-author)

REPRINT LISTING

Page 22

(MASTER)

1- MISSING

Year/Number <i>Vol./Page</i>	Title	Primary Author
<u>80-215</u> <i>III-215</i>	Standardized Terminology for Oxide Charges Associated with Thermally Oxidized Silicon	DEAL, B.E.
<u>81-216</u> <i>III-216</i>	Interface States and Electron Spin Resonance Centers in Thermally Oxidized (111) and (100) Silicon Wafers	DEAL, B.E.
<u>81-217</u> <i>III-217</i>	Rapid Technique to Determine Extent of Pt-Si Reaction in Very Thin Films	LANDAU, B.
<u>81-218</u> <i>III-218</i>	A Four-Phase Complex Refractive Index Model of Ion-Implantation Damage: Optical Constants of Phosphorus Implants in Silicon	DELFINO, M.
<u>81-219</u> <i>7 NOT FOUND</i>	<i>MISSING</i> Optical Characterization of Tungsten Silicide Thin Films	DELFINO, M.
<u>81-220</u> <i>III-220</i>	Microstructure Fabrication in Electronic Devices	DEAL, B.E.
<u>82-221</u> <i>III-221</i>	Oxide Charges Induced in Thermal Silicon Dioxide by Scanning Electron and Laser Beam Annealing	RAZOUK, R.R.
<u>82-222</u> <i>III-222</i>	Kinetics of High Pressure Oxidation of Silicon in Pyrogenic Steam	RAZOUK, R.R.
<u>82-223</u> <i>III-223</i>	Optical Constants of Arsenic and Boron Implants in Silicon Determined by a Four-Phase Complex Refractive Index Model	DELFINO, M.

REPRINT LISTING
(Master)

Page 23

Year/Number	<i>VOL/PAGE</i>	Title	Primary Author
82-224	<i>III-224</i>	Thermal Oxidation and Chemical Vapor Deposition of Insulators	DEAL, B.E.
82-225	<i>III-225</i>	The Thermal Oxidation of Silicon	DEAL, B.E.
82-226	<i>III-226</i>	CO Laser Annealing of Arsenic-Implanted Silicon	DELFINO, M.
82-227	<i>III-227</i>	Laser Activated Flow of Phospho-silicate Glass in Integrated Circuit Devices	DELFINO, M.
82-228	<i>III-228</i>	High Pressure Oxidation of Silicon in Dry Oxygen	LIE, L.N.
82-229	<i>III-229</i>	Hydrogen Anneal Effects on Metal-Semiconductor Work Function Difference	RAZOUK, R.R.
82-230	<i>III-230</i>	Oxidation of Tantalum Disilicide/ Polycrystalline Silicon Structures in Dry O ₂	RAZOUK, R.R.
83-231	<i>III-231</i>	Characteristics of TaSi ₂ /Poly-Si Films Oxidized in Steam for VLSI Applications	DeBLASI, J.M.
83-232	<i>III-232</i>	cw Laser Activated Flow Applied to the Planarization of Metal-Oxide-Semiconductor Field-Effect Transistor Structures	DELFINO, M.

REPRINT LISTING
(Master)

Page 24

Year/Number	Title	Primary Author
83-233 Vol. / PAGE II - 233	Phosphosilicate Glass Flow Over Aluminum in Integratee Circuit Devices	DELFINO, M.
83-234 II - 234	Effect of Argon Implantation on the Activation of Boron Implanted in Silicon	MILGRAM, A.
83-235 II - 235	Laser Activated Flow for Integrated Circuit Fabrication	DELFINO, M.
87-236 III - 236	The Physics and Chemistry of Thin Native Oxide Films on Silicon	DEAL, B.E.